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SEMICONDUCTOR

November 2013

FQPF9P25 — P-Channel QFET<sup>®</sup> MOSFET

## FQPF9P25

## **P-Channel QFET® MOSFET**

-250 V, -6 A, 620 mΩ

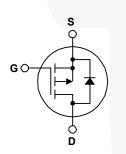
### Description

This P-Channel enhancement mode power MOSFET is • -6 A, -250 V,  $R_{DS(on)}$  = 620 m $\Omega$  (Max.) @ V<sub>GS</sub> = -10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state • Low Gate Charge (Typ. 29 nC) resistance, and to provide superior switching performance . Low Crss (Typ. 27 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications.

#### Features

- I<sub>D</sub> = -3 A





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

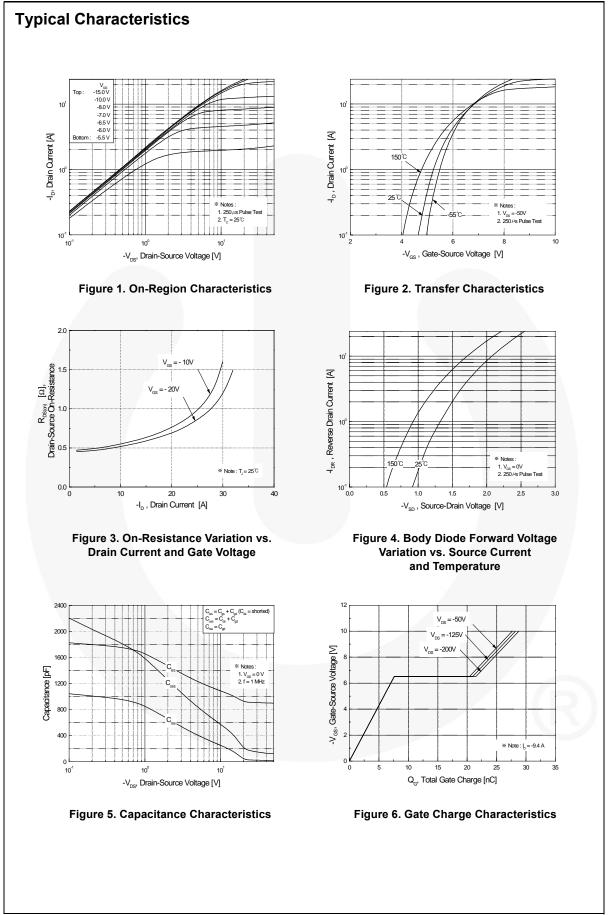
Symbol	Parameter		FQPF9P25	Unit
V <sub>DSS</sub>	Drain-Source Voltage		-250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		-6.0	А
	- Continuous (T <sub>C</sub> = 100°C)		-3.9	A
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-24	A
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	650	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-6.0	A
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-5.5	V/ns
P <sub>D</sub>	Power Dissipation ( $T_C = 25^{\circ}C$ )		50	W
	- Derate above 25°C		0.4	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

## **Thermal Characteristics**

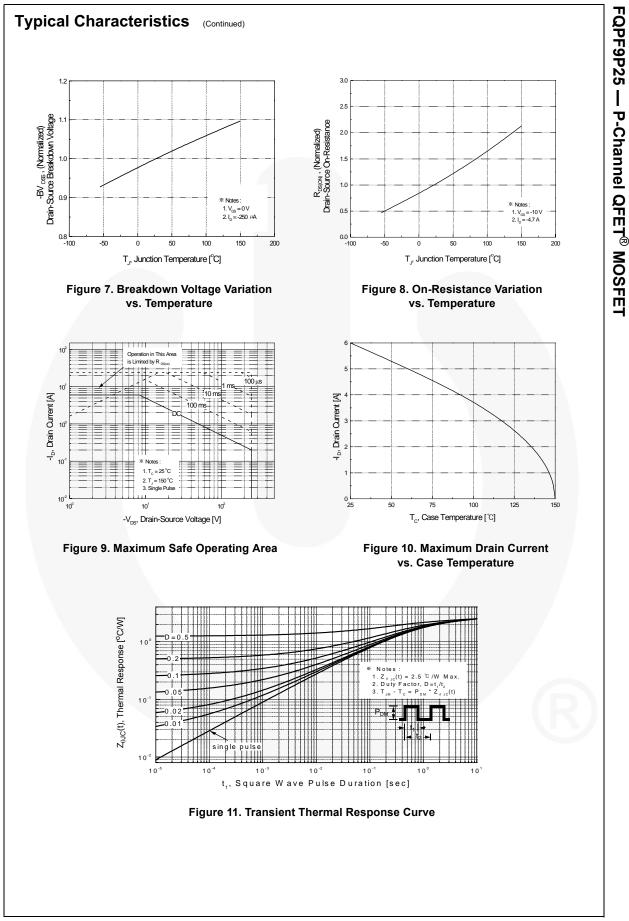
Symbol	Parameter	FQPF9P25	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	2.5	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

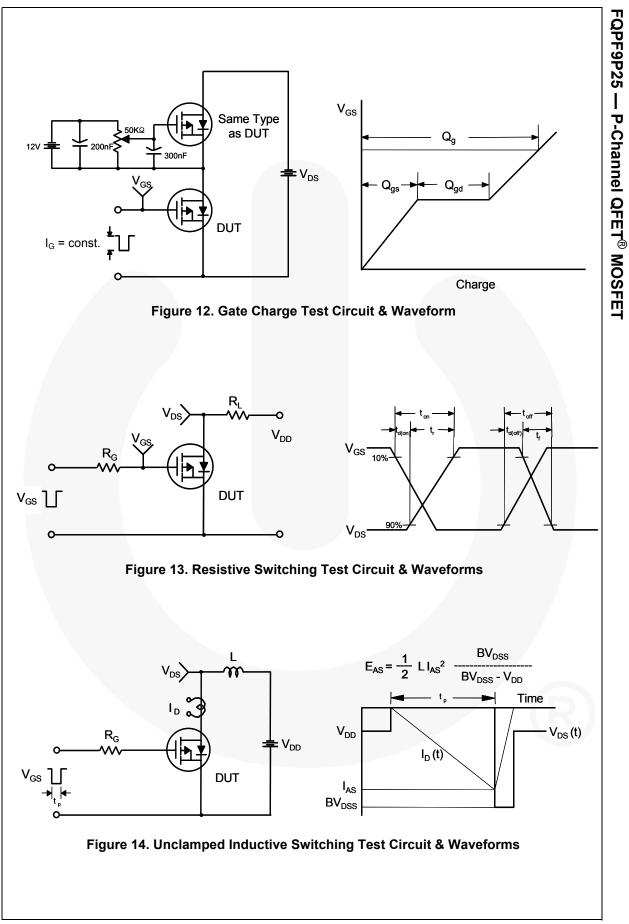
Part N	Part Number Top Mark Pac		Pack	kage Packing Method Reel		el Size	Tape Width		Quantity	
		220F Tube N/		N/A	N/A		50 units			
lectrie	cal Cha	racteristics	T <sub>C</sub> = 25°C	C unless othe	erwise noted.					
Symbol		Parameter			Test Condition	IS	Min.	Тур.	Max.	Unit
Off Cha	aracterist	tics								
3V <sub>DSS</sub>	Drain-Sou	Irce Breakdown Vol	tage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = -250 μA			-250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient		$I_D = -250 \ \mu$ A, Referenced to 25°C			C	-0.2		V/°C	
DSS				V <sub>DS</sub> = -	250 V, V <sub>GS</sub> = 0 V	/			-1	μA
	Zero Gate	e Voltage Drain Curr	rent	V <sub>DS</sub> = -	200 V, T <sub>C</sub> = 125	°C			-10	μA
GSSF	Gate-Bod	y Leakage Current,	Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$					-100	nA
GSSR	Gate-Bod	y Leakage Current,	Reverse	V <sub>GS</sub> = 3	80 V, V <sub>DS</sub> = 0 V				100	nA
On Cha	racterist	ics							I	
/ <sub>GS(th)</sub>		eshold Voltage	_		/ <sub>GS</sub> , I <sub>D</sub> = -250 μ/	4	-3.0		-5.0	V
R <sub>DS(on)</sub>		in-Source	_	_	10 V, I <sub>D</sub> = -3.0 A			0.48	0.62	Ω
JFS		Forward Transconductance			40 V, I <sub>D</sub> = -3.0 A			4.8		S
10			_	00						1
Dynam	ic Chara	cteristics								
C <sub>iss</sub>	Input Cap	acitance		$V_{DS} = -$	25 V, V <sub>GS</sub> = 0 V,			910	1180	pF
C <sub>oss</sub>	Output Ca	utput Capacitance everse Transfer Capacitance		f = 1.0  MHz			170	220	pF	
C <sub>rss</sub>	Reverse							27	35	pF
				1					1	
Switch	ing Char	acteristics								
d(on)	Turn-On [	Delay Time		Vpp = -	125 V, I <sub>D</sub> = -9.4	Δ		20	50	ns
r	Turn-On F	Rise Time		$R_G = 25$		<i>,</i> ,		150	310	ns
d(off)	Turn-Off [	Delay Time		G				45	100	ns
f	Turn-Off F	all Time				(Note 4)		65	140	ns
ე <sup>g</sup>	Total Gate	e Charge		$V_{DS} = -$	200 V, I <sub>D</sub> = -9.4	A,		29	38	nC
ସୁ <sub>gs</sub>	Gate-Sou	rce Charge		V <sub>GS</sub> = -				7.6		nC
Q <sub>gd</sub>	Gate-Drai	Gate-Drain Charge		(Note 4)				14		nC
Drain-S	Source Di	iode Character	istics ar	nd Maxi	imum Rating	js				
S	Maximum	Continuous Drain-S	Source Dic	ode Forwa	ard Current				-6.0	А
SM	Maximum	Pulsed Drain-Source	ce Diode F	orward C	urrent				-24	Α
√ <sub>SD</sub>	Drain-Sou	Irce Diode Forward	Voltage	$V_{GS} = 0$	) V, I <sub>S</sub> = -6.0 A				-5.0	V
rr	Reverse F	Recovery Time		$V_{GS} = 0$	) V, I <sub>S</sub> = -9.4 A,			190		ns
ე <sub>rr</sub>	Reverse F	Recovery Charge		dl <sub>F</sub> / dt	= 100 A/μs			1.45		μC
L = 28.9 m I <sub>SD</sub> $\leq$ -9.4	H, $I_{AS}$ = -6.0 A, A, di/dt $\leq$ 300 /	dth limited by maximum ju $V_{DD} = -50 V$ , $R_G = 25 \Omega$ , s $A/\mu s$ , $V_{DD} \leq BV_{DSS}$ , start operating temperature.	tarting T <sub>J</sub> = 2	5°C.						

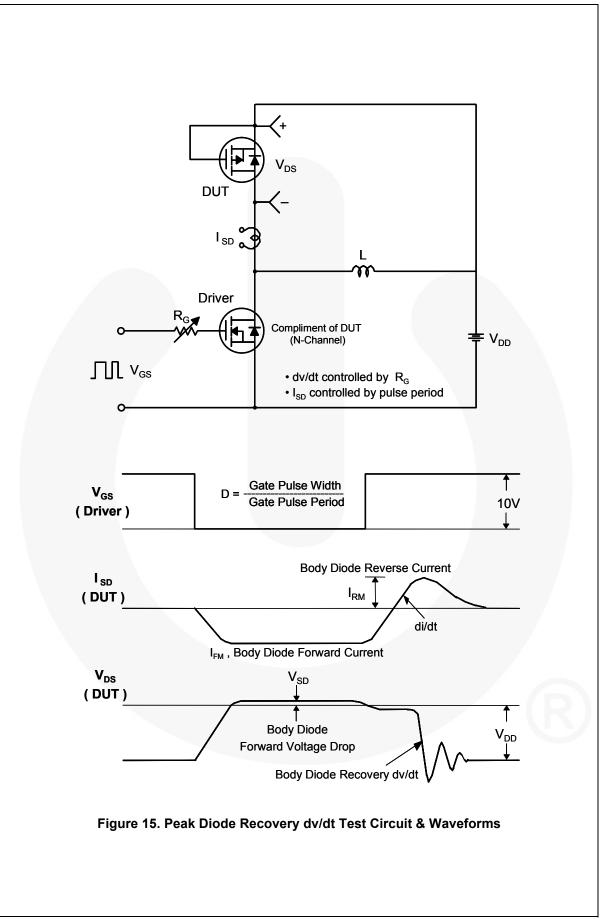
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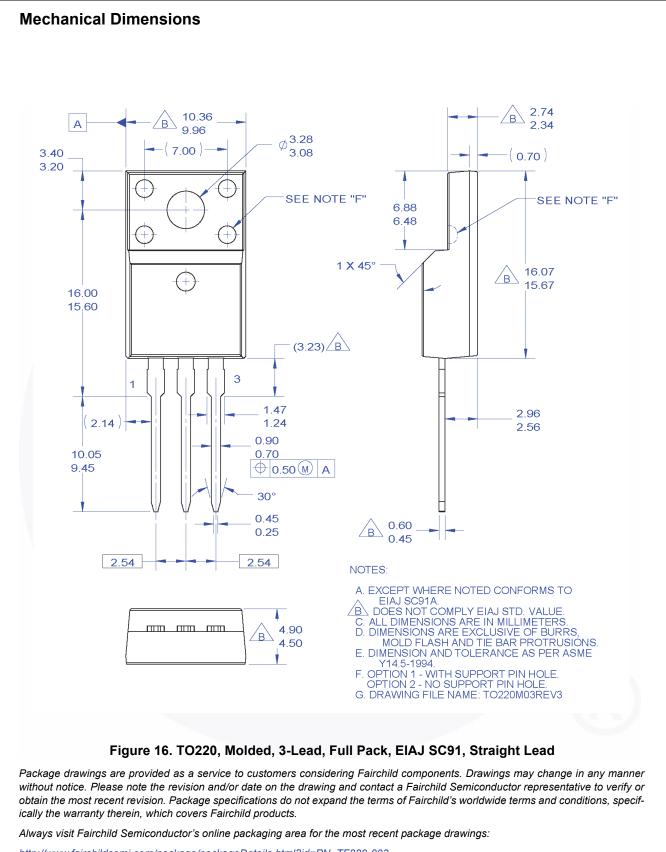


FQPF9P25 — P-Channel QFET<sup>®</sup> MOSFET









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